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Analysis of Artificial Dielectric Layers with Finite Conductivity

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Artificial Dielectric Layers



Anisotropy is a key property to avoid surface waves

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Solution to surface waves





Applications for antennas

Improve efficiency of on-chip antennas



prototype

Wide-band wide-scan phased array



6 -15 GHz

No surface waves

Scan to 60 deg. on H-plane and 80 deg. on E-plane with no scan blindness

Analysis of ADL

D. Cavallo, W. H. Syed and A. Neto, 'Part-I', *IEEE TAP*, 61-3, 2014 D. Cavallo, W. H. Syed and A. Neto, 'Part-II', *IEEE TAP*, 61-3, 2014

Closed-form expression for aligned layers





D. Cavallo and C. Felita, TAP, 65-10, 2017



Shift between layers



Equivalent circuit





Validation formulas



Plane wave incidence 5 layers $s_x = s_y = 0.25d_x$



Equivalent circuit provides S-parameters

- Generic plane wave incidence
- Arbitrary small distance
- Arbitrary number of layers

Ohmic losses in ADLs





Answer: very low because the patches are sub-wavelength

More quantitative answer: o.8 dB losses at 300 GHz



300 GHz prototype

- However, losses depends on
 - How the ADL is illuminated
 e.g. plane wave or near source
 - Polarization and direction of the incident field

Goal: quantify analytically the losses due to finite conductivity

Generalization to lossy metal



Equivalent circuit for lossy metal



Equivalent layer impedances are in the form

$$Y_{\infty TE} \approx 2 \sum_{m_y \neq 0} |\operatorname{sinc}(k_{ym}w/2)|^2 S_{\infty} \left(\frac{k_{x0}^2}{2k_{ym}^2} \left(\frac{\zeta_0 k_0}{k_{zm}} + 2Z_s S_{\infty} \right)^{-1} + \left(\frac{\zeta_0 k_{zm}}{k_0} + 2Z_s S_{\infty} \right)^{-1} \right)$$

$$S_{\infty} = -j\cot(\frac{-j2\pi|m|d_z}{d}) + je^{j2\pi m\frac{s}{d}}\csc(\frac{-j2\pi|m|d_z}{d})$$

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Single layer: losses



Validation







What are the losses for near source illumination?





$l_{\rm slot} = d_{\rm slot} = 750 \mu {\rm m}$	$\delta_{ m slot} = 100 \mu m$
$w_{\rm slot} = 50 \mu{\rm m}$	$h = 50 \mu m$

4 layers
$$\sigma = 10^7 \frac{\text{S}}{\text{m}}$$



Effective constitutive parameters

D. Cohen and R. Shavit, IEEE TAP, 63-5, 2015.





Double slot with ADLs



Efficiency of 200GHz antenna



- No TM surface wave propagates in the structure
- TE modes, responsible for magnetic losses, are below cutoff
- Higher losses if ADLs used for guiding waves, when TE modes propagate



dB(max ¥/m) -20 —<mark>—</mark>

> -21.8 -23.6 -25.5

> -27.3

)eitt





ANALYTICAL SPECTRUM OF ARTIFICIAL DIELECTRIC LAYERS (FINITE σ)



- Analytical description of the dissipation losses
- Effective **electric and magnetic** $\tan \delta$ can be retrieved

3 MAIN MESSAGES

1) Magnetic losses much higher than electric one (current loops)

2) Magnetic losses are excited by TE mode propagating in the structure

3) Our applications of ADLs does not involve TE modes (very high efficiency)